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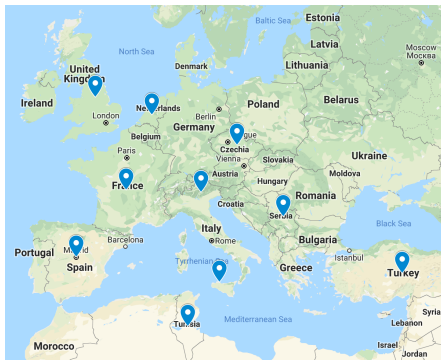
MINISTRY OF EDUCATION,  
YOUTH AND SPORTS

# Predicting Tribological Properties of Low-Dimensional Materials

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CTU in Prague**

# Advanced Materials Group



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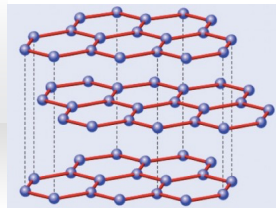
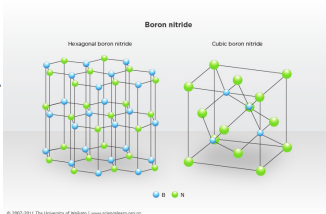
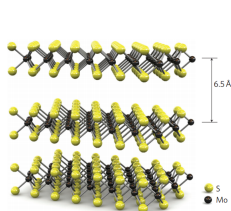
**Ass't Prof:** Antonio Cammarata 🇮🇹 🇮🇹, Paolo Nicolini 🇮🇹 🇮🇹

**Postdocs:** Emilio Frutos 🇪🇸, Alberto Fraile 🇪🇸, Benjamin Irving 🇬🇧, Hakan Yavas 🇹🇷, Sener Sen 🇹🇷, Kosta Simonovic 🇮🇯, Diego Lopez 🇪🇸

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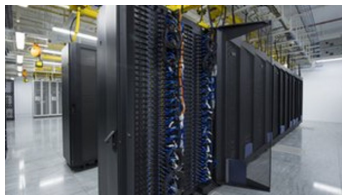
- Self-adaptive low-friction coatings [WSC; WSeC; MoSC; MoSeC]
- High temperature tribology
- Biocompatible coatings
- Interface design of crystalline materials with improved radiation damage resistance
- **Modelling & Simulations** e.g. TMD; h-BN; ZnO; Graphene



- Methods generally fall into two distinct categories:
- **Quantum:** uses quantum physics; suitable for smaller systems (10-100s of atoms) parameter-free (can do 'brand new' chemistry & physics); computationally intensive
- **Classical:** uses classical physics; suitable for larger systems ( $10^2 - 10^6$  of atoms); computationally less intensive; no electronic properties; may be less accurate
- In Advanced Materials Group we combine both methods



# Studying materials *in silico*



- Simulation packages: LAMMPS, VASP, ABINIT, SIESTA...
- High Performance Computing clusters (ca.  $10^7$  CPU hrs):  
**Anselm/Salomon**, IT4I, Ostrava, CZ  
**Iridis**, University of Southampton, UK  
**Eagle**, Poznań, Poland

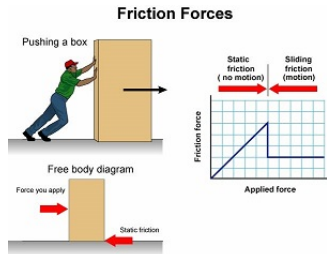


- CODFISH (2,5 M); ENDFISH (0,5 M)
- HOLDEM (2,23 M)
- OPTOSILICA (0,5 M)
- FATRADEX (2,5 M)
- NanoTribo (1,5 M)
- ATRIO (3,03 M)
- RATONMO (2,83 M)
- AFAM (2,706 M)

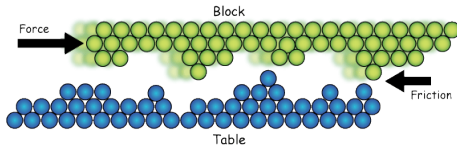


# Background

- **Friction:** a force that resists sliding or rolling of one object over another; both a necessity and a disadvantage
- **Tribology:** from Greek *τριβω* ('I rub') + *λογία* ('study of'); the multidisciplinary (engineering, metallurgy, chemistry) study of interactions between sliding surfaces



study.com

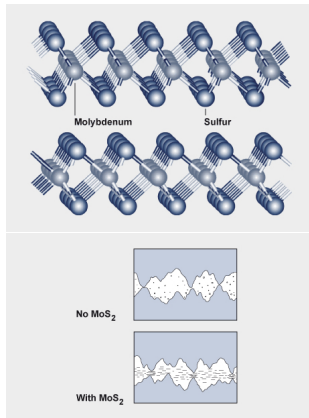
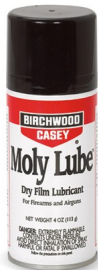


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# TMDs - structure & lubricating properties [AMG]

- $MX_2$  family of compounds, where  $M = Mo, W$ ;  $X = S, Se, Te$
- Molybdenum disulfide,  $MoS_2$ , best known example





# TMDs - structure & physicochemical properties

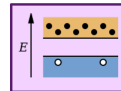
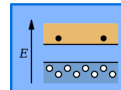
**Periodic Table of the Elements**

p-type MoS<sub>2</sub>                      n-type MoS<sub>2</sub>

The periodic table shows the following highlights:

- p-type MoS<sub>2</sub>** (blue box): Group 16, Period 4 (Selenium, Se, atomic number 34).
- n-type MoS<sub>2</sub>** (red box): Group 16, Period 5 (Tellurium, Te, atomic number 52).

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holmstrom@uoregon.edu

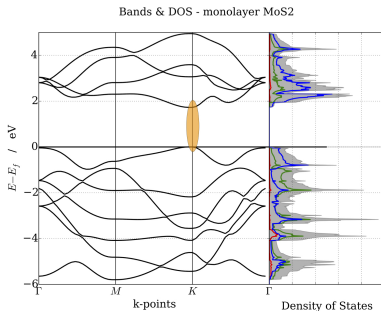
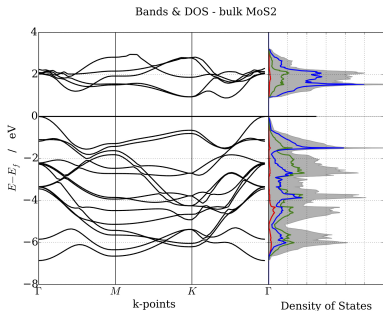


- We have a variety of stoichiometries available, each offering unique properties
- We can explore/improve their properties using both experiments and theory

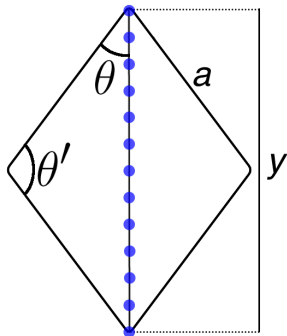
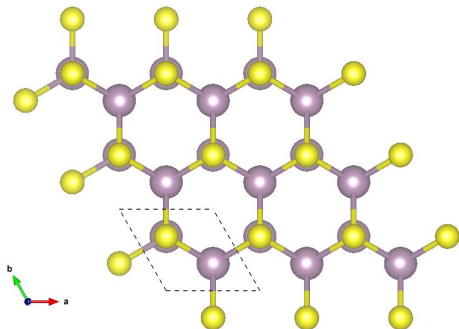


# Homogeneous TMDs

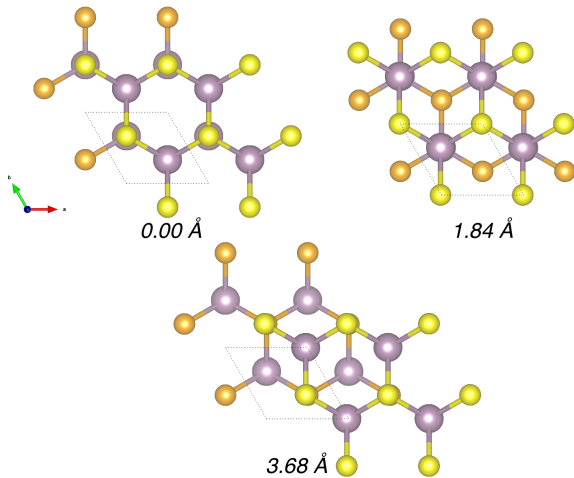
- Layer-dependent properties of TMDs have attracted much attention e.g. MoS<sub>2</sub> transition from indirect (1.3 eV) to direct bandgap (1.8 eV):



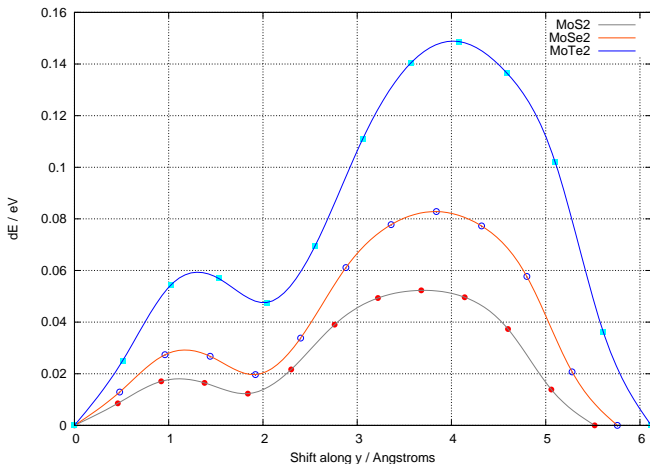
Recent work - DFT calculations to investigate sliding properties of TMDs



Most important geometric configurations for  $\text{MX}_2$  bilayers:



Potential energy profiles for MoX<sub>2</sub> bilayers:



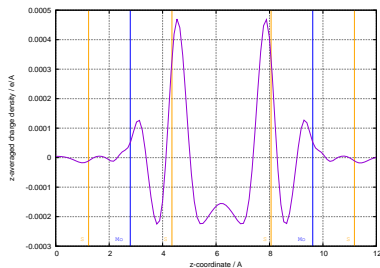
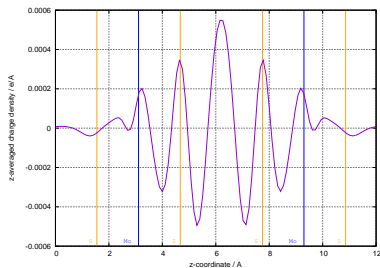
**Table:** Nanomechanical properties calculated for each TMD bilayer

TMD	$E_{\text{bind}} / \text{meV (per cell)}$	$\gamma / \text{Jm}^{-2}$	$f_{\text{max}} / \text{eV/\AA}$	$\tau_y / \text{GPa}$
MoS <sub>2</sub>	<b>149.058</b>	<b>0.271</b>	<b>0.037738</b>	<b>0.6853</b>
MoSe <sub>2</sub>	218.230	0.366	0.056833	0.9536
MoTe <sub>2</sub>	332.902	0.493	0.081934	1.2145
WS <sub>2</sub>	267.337	0.490	0.064125	1.1748
WSe <sub>2</sub>	333.132	0.559	0.081275	1.3631
WTe <sub>2</sub>	440.756	0.657	0.099769	1.4874

- $E_{\text{bind}} = E_{\text{bi}} - (2 \times E_{\text{mono}})$
- $\gamma = E_{\text{bind}}/A$
- $f_{\text{max}} = dE/dy$
- $\tau_y = f_{\text{max}}/A$



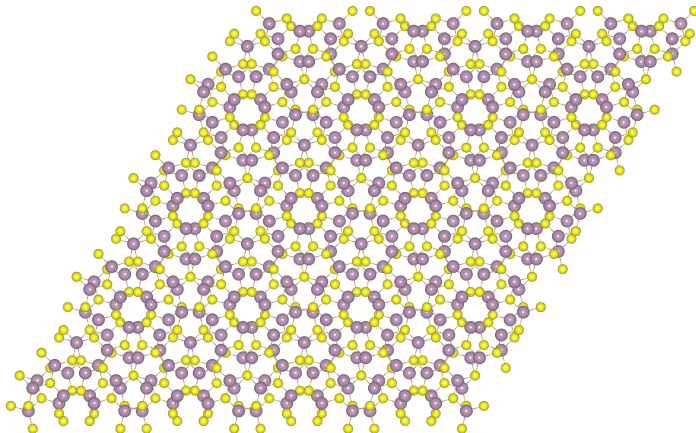
z-averaged charge density difference plots for MoS<sub>2</sub>:



- $E_{\min}$ : charge accumulation at interface
- $E_{\max}$ : charge accumulation at chalcogens only
- Perhaps we can use fundamental properties to predict tribo behaviour
- $\chi_{\text{Mo}} = 2.16$ ,  $\chi_{\text{W}} = 2.36$ ;  $\chi_{\text{S}} = 2.58$ ,  $\chi_{\text{Se}} = 2.55$ ,  $\chi_{\text{Te}} = 2.10$

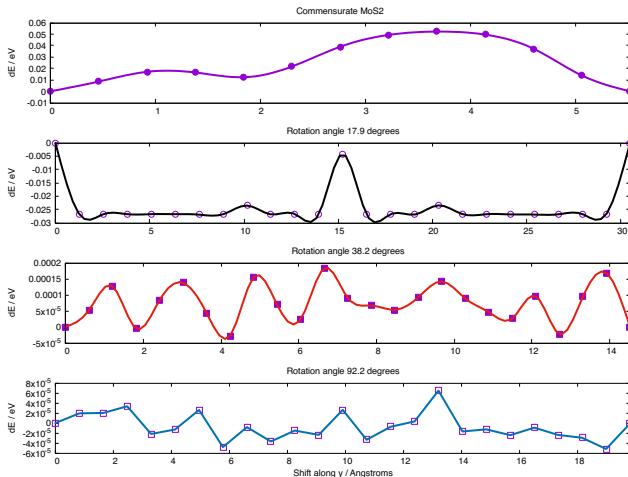


Top-down projection of *incommensurate accidentally commensurate* MoS<sub>2</sub> bilayer (top layer rotated 92.2° about z-axis):





The effect(s) of incommensuration have also been studied for MoS<sub>2</sub>; it is shown that a greater degree of incommensuration results in a significant drop in calculated values of  $\tau_y$  (*i.e.*, easier inter-plane shear)



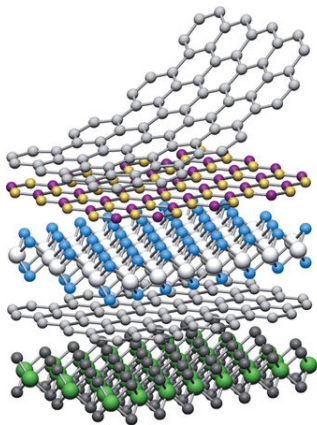
Again using the PES we can calculate the *ideal shear strength*,  $\tau_y$ , for which a lower value indicates easier sliding:

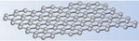

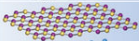



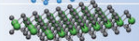

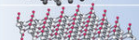

**Table:** Nanomechanical properties calculated for each of the (in)commensurate MoS<sub>2</sub> bilayers

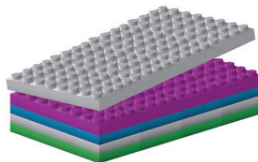
Angle of Rotation	$E_{\text{bind}} / \text{meV}$ (per MoS <sub>2</sub> )	$\gamma / \text{Jm}^{-2}$	$f_{\text{max}} / \text{eV}/\text{\AA}$	$\tau_y / \text{GPa}$
0.00	74.529	0.271	0.037738	0.6853
17.9	57.131	0.212	0.008902	0.0127
38.2	58.757	0.218	0.000105	0.0008
92.2	58.849	0.218	0.000043	0.0001



# Van der Waals Heterostructures

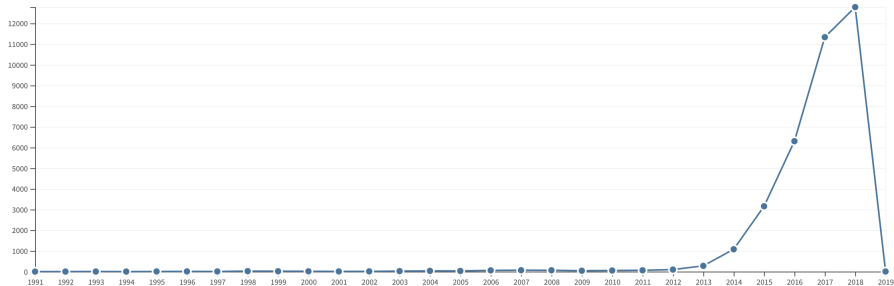


	Graphene	
	hBN	
	MoS <sub>2</sub>	
	WSe <sub>2</sub>	
	Fluorographene	

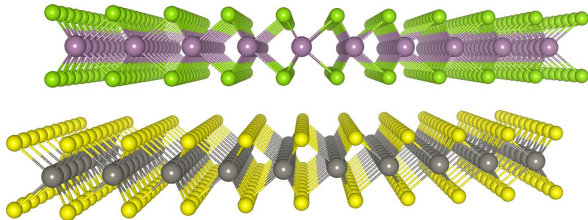


## WOS search results “van der Waals heterostructures”:

Sum of Times Cited per Year



# Van der Waals Heterostructures

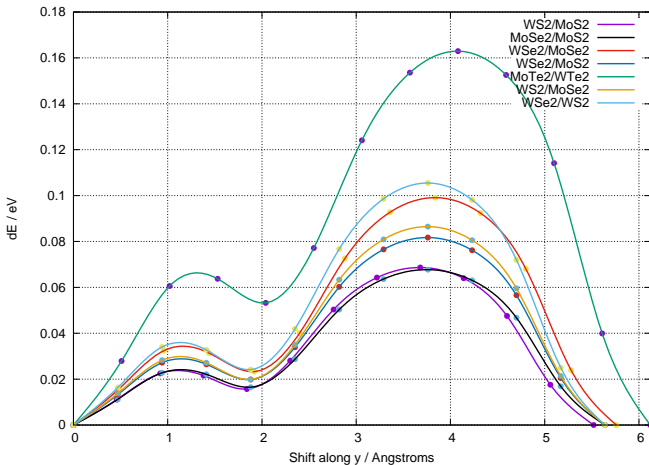


MoSe<sub>2</sub>-on-WS<sub>2</sub> vdW

- Can offer excellent semiconducting properties and strong-light matter interactions
  - Power conversion efficiency enhancers
  - Photoactive layer
- Scalable fabrication still a big obstacle
  - Require sound understanding of nanomechanical properties. . .



# Van der Waals Heterostructures - PES calculations



# Van der Waals Heterostructures - PES calculations

TMD	$E_{\text{bind}}$ / meV (per cell)	$\gamma/\text{Jm}^{-2}$	$f_{\text{max}}$ / eV/Å	$\tau_y/\text{GPa}$
MoS <sub>2</sub>	149.058	0.271	0.037738	0.6853
MoSe <sub>2</sub>    MoS <sub>2</sub>	182.161	0.319	0.046099	0.8065
WS <sub>2</sub>    MoS <sub>2</sub>	198.755	0.362	0.048498	0.8830
MoSe <sub>2</sub>	218.230	0.366	0.056833	0.9536
WSe <sub>2</sub>    MoS <sub>2</sub>	225.831	0.394	0.055964	0.9775
WS <sub>2</sub>    MoSe <sub>2</sub>	240.856	0.421	0.060308	1.0546
WSe <sub>2</sub>    MoSe <sub>2</sub>	268.694	0.449	0.067703	1.1326
WS <sub>2</sub>	267.337	0.490	0.064125	1.1748
MoTe <sub>2</sub>	332.902	0.493	0.081934	1.2145
WSe <sub>2</sub>    WS <sub>2</sub>	300.199	0.524	0.074150	1.2946
MoTe <sub>2</sub>    WTe <sub>2</sub>	381.674	0.563	0.092021	1.3571
WSe <sub>2</sub>	333.132	0.559	0.081275	1.3631
WTe <sub>2</sub>	440.756	0.657	0.099769	1.4874

- Now formulating relationship between electronic properties of vdW systems and nanomechanical properties



# Acknowledgements

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**Thank you for your attention**

